

# MMBT4403LT1

## Switching Transistor

### PNP Silicon

#### Features

- Pb-Free Package is Available

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	–40	Vdc
Collector–Base Voltage	$V_{CBO}$	–40	Vdc
Emitter–Base Voltage	$V_{EBO}$	–5.0	Vdc
Collector Current – Continuous	$I_C$	–600	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	–55 to +150	$^\circ\text{C}$

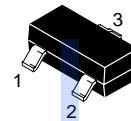
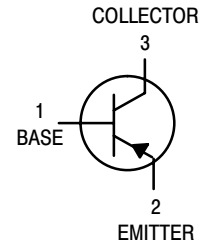
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR–5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



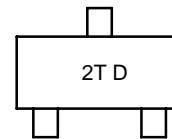
ON Semiconductor®

<http://onsemi.com>



SOT–23 (TO–236)  
CASE 318–08  
STYLE 6

#### MARKING DIAGRAM



2T = Specific Device Code  
D = Date Code

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

# MMBT4403LT1

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (Note 3) (I <sub>C</sub> = –1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	–40	–	V <sub>dc</sub>
Collector–Base Breakdown Voltage (I <sub>C</sub> = –0.1 mA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	–40	–	V <sub>dc</sub>
Emitter–Base Breakdown Voltage (I <sub>E</sub> = –0.1 mA <sub>dc</sub> , I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	–5.0	–	V <sub>dc</sub>
Base Cutoff Current (V <sub>CE</sub> = –35 V <sub>dc</sub> , V <sub>EB</sub> = –0.4 V <sub>dc</sub> )	I <sub>BEV</sub>	–	–0.1	μA <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = –35 V <sub>dc</sub> , V <sub>EB</sub> = –0.4 V <sub>dc</sub> )	I <sub>CEX</sub>	–	–0.1	μA <sub>dc</sub>

## ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = –0.1 mA <sub>dc</sub> , V <sub>CE</sub> = –1.0 V <sub>dc</sub> ) (I <sub>C</sub> = –1.0 mA <sub>dc</sub> , V <sub>CE</sub> = –1.0 V <sub>dc</sub> ) (I <sub>C</sub> = –10 mA <sub>dc</sub> , V <sub>CE</sub> = –1.0 V <sub>dc</sub> ) (I <sub>C</sub> = –150 mA <sub>dc</sub> , V <sub>CE</sub> = –2.0 V <sub>dc</sub> ) (Note 3) (I <sub>C</sub> = –500 mA <sub>dc</sub> , V <sub>CE</sub> = –2.0 V <sub>dc</sub> ) (Note 3)	h <sub>FE</sub>	30 60 100 100 20	– – – 300 –	–
Collector–Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = –150 mA <sub>dc</sub> , I <sub>B</sub> = –15 mA <sub>dc</sub> ) (I <sub>C</sub> = –500 mA <sub>dc</sub> , I <sub>B</sub> = –50 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	– –	–0.4 –0.75	V <sub>dc</sub>
Base–Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = –150 mA <sub>dc</sub> , I <sub>B</sub> = –15 mA <sub>dc</sub> ) (I <sub>C</sub> = –500 mA <sub>dc</sub> , I <sub>B</sub> = –50 mA <sub>dc</sub> )	V <sub>BE(sat)</sub>	–0.75 –	–0.95 –1.3	V <sub>dc</sub>

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (I <sub>C</sub> = –20 mA <sub>dc</sub> , V <sub>CE</sub> = –10 V <sub>dc</sub> , f = 100 MHz)	f <sub>T</sub>	200	–	MHz
Collector–Base Capacitance (V <sub>CB</sub> = –10 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>cb</sub>	–	8.5	pF
Emitter–Base Capacitance (V <sub>BE</sub> = –0.5 V <sub>dc</sub> , I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>eb</sub>	–	30	pF
Input Impedance (I <sub>C</sub> = –1.0 mA <sub>dc</sub> , V <sub>CE</sub> = –10 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>ie</sub>	1.5	15	kΩ
Voltage Feedback Ratio (I <sub>C</sub> = –1.0 mA <sub>dc</sub> , V <sub>CE</sub> = –10 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>re</sub>	0.1	8.0	X 10 <sup>–4</sup>
Small–Signal Current Gain (I <sub>C</sub> = –1.0 mA <sub>dc</sub> , V <sub>CE</sub> = –10 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>fe</sub>	60	500	–
Output Admittance (I <sub>C</sub> = –1.0 mA <sub>dc</sub> , V <sub>CE</sub> = –10 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>oe</sub>	1.0	100	μmhos

## SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = –30 V <sub>dc</sub> , V <sub>EB</sub> = –2.0 V <sub>dc</sub> , I <sub>C</sub> = –150 mA <sub>dc</sub> , I <sub>B1</sub> = –15 mA <sub>dc</sub> )	t <sub>d</sub>	–	15	ns
Rise Time		t <sub>r</sub>	–	20	
Storage Time	(V <sub>CC</sub> = –30 V <sub>dc</sub> , I <sub>C</sub> = –150 mA <sub>dc</sub> , I <sub>B1</sub> = I <sub>B2</sub> = –15 mA <sub>dc</sub> )	t <sub>s</sub>	–	225	ns
Fall Time		t <sub>f</sub>	–	30	

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

# MMBT4403LT1

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBT4403LT1	SOT-23 (TO-236)	3000 Tape & Reel
MMBT4403LT1G	SOT-23 (TO-236) (Pb-Free)	3000 Tape & Reel
MMBT4403LT3	SOT-23 (TO-236)	10,000 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## SWITCHING TIME EQUIVALENT TEST CIRCUIT

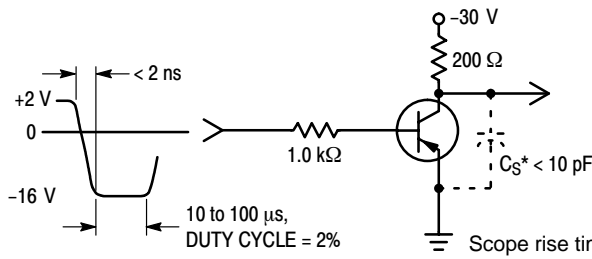


Figure 1. Turn-On Time

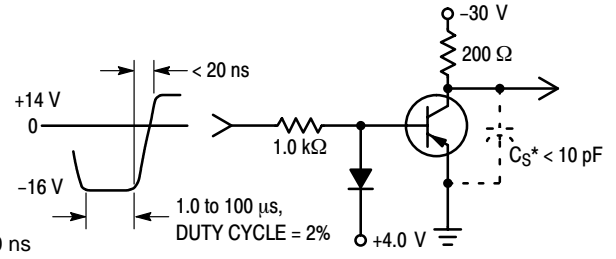


Figure 2. Turn-Off Time

\*Total shunt capacitance of test jig connectors, and oscilloscope

# MMBT4403LT1

## TRANSIENT CHARACTERISTICS

— 25°C    - - - 100°C

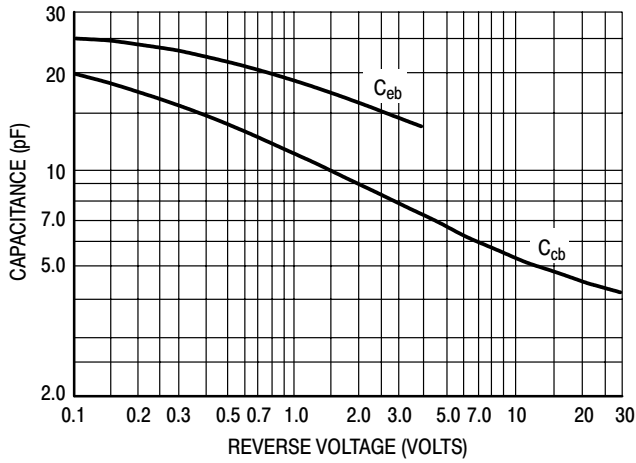


Figure 3. Capacitances

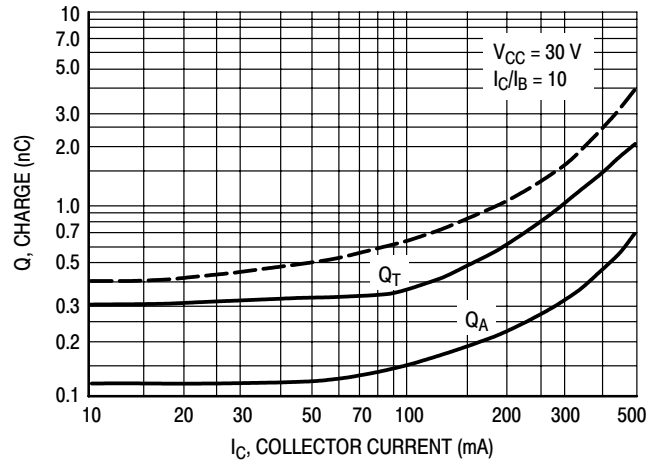


Figure 4. Charge Data

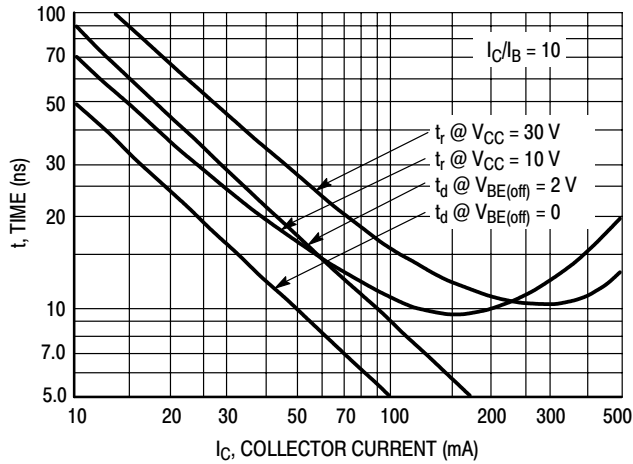


Figure 5. Turn-On Time

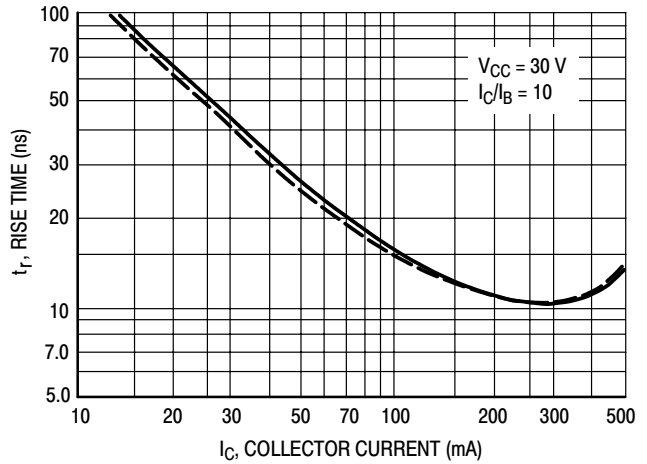


Figure 6. Rise Time

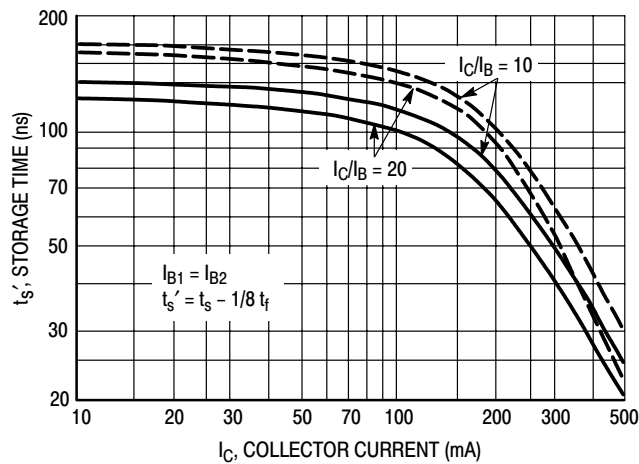


Figure 7. Storage Time

# MMBT4403LT1

## SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

$V_{CE} = -10 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ ; Bandwidth = 1.0 Hz

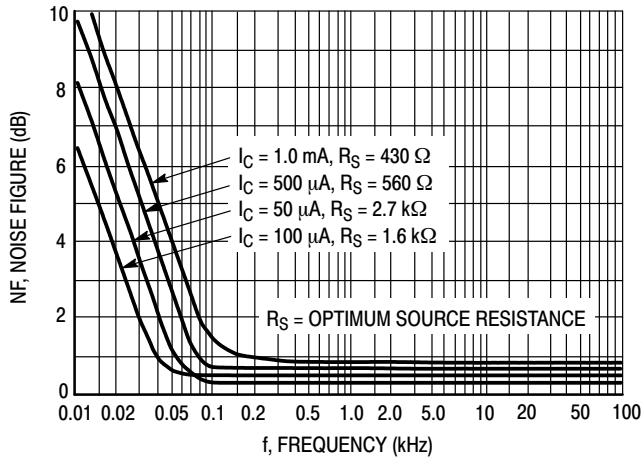


Figure 8. Frequency Effects

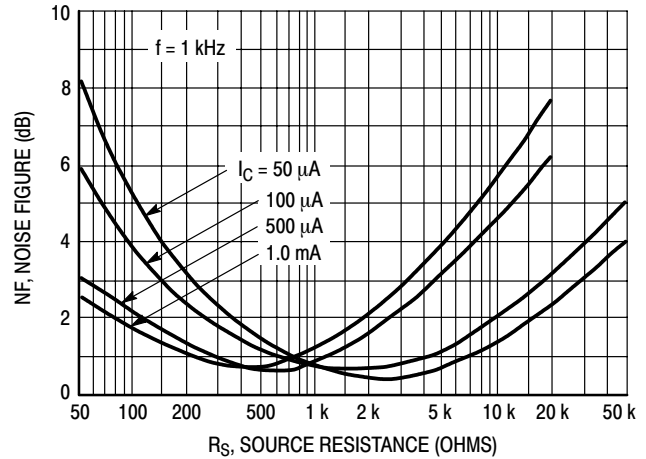


Figure 9. Source Resistance Effects

## h PARAMETERS

$V_{CE} = 10 \text{ Vdc}$ ,  $f = 1.0 \text{ kHz}$ ,  $T_A = 25^\circ\text{C}$

This group of graphs illustrates the relationship between  $h_{fe}$  and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4403LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

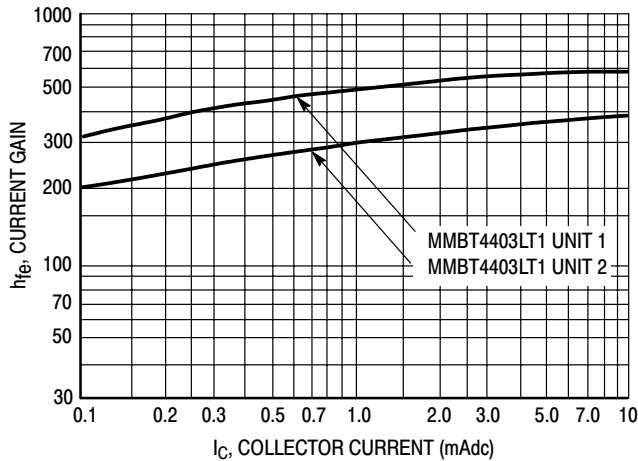


Figure 10. Current Gain

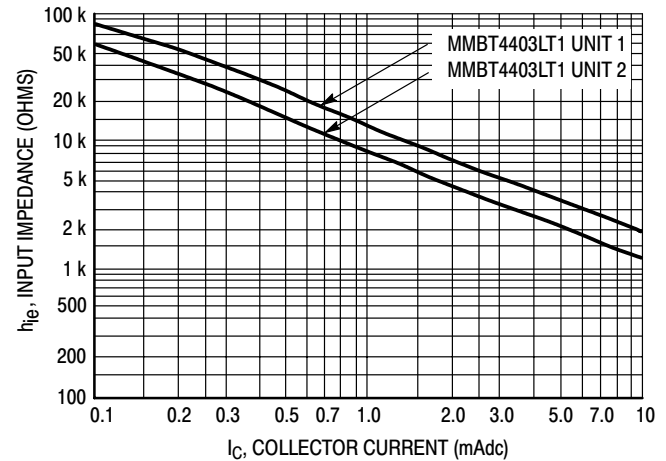


Figure 11. Input Impedance

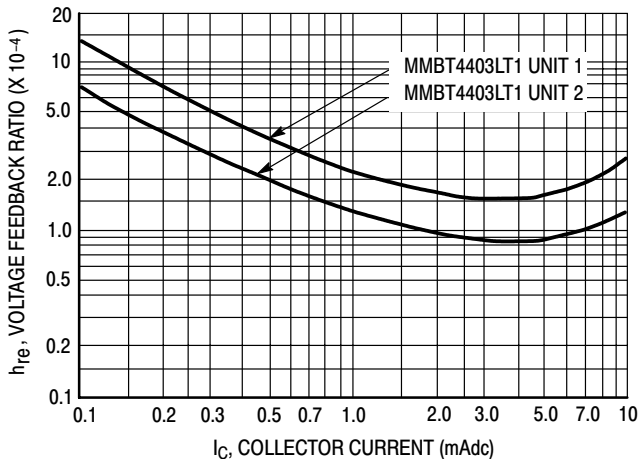


Figure 12. Voltage Feedback Ratio

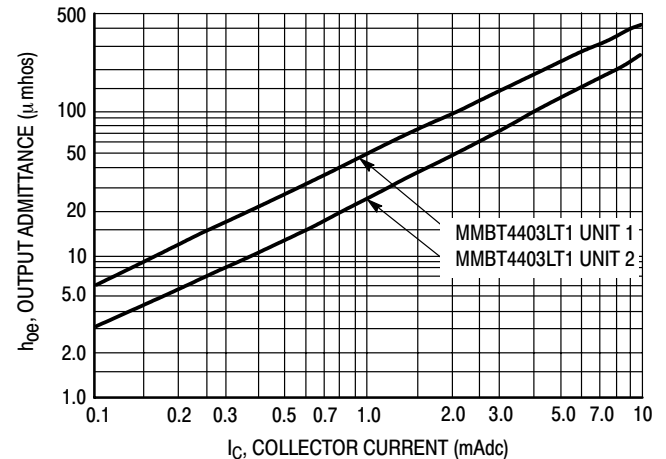


Figure 13. Output Admittance

# MMBT4403LT1

## STATIC CHARACTERISTICS

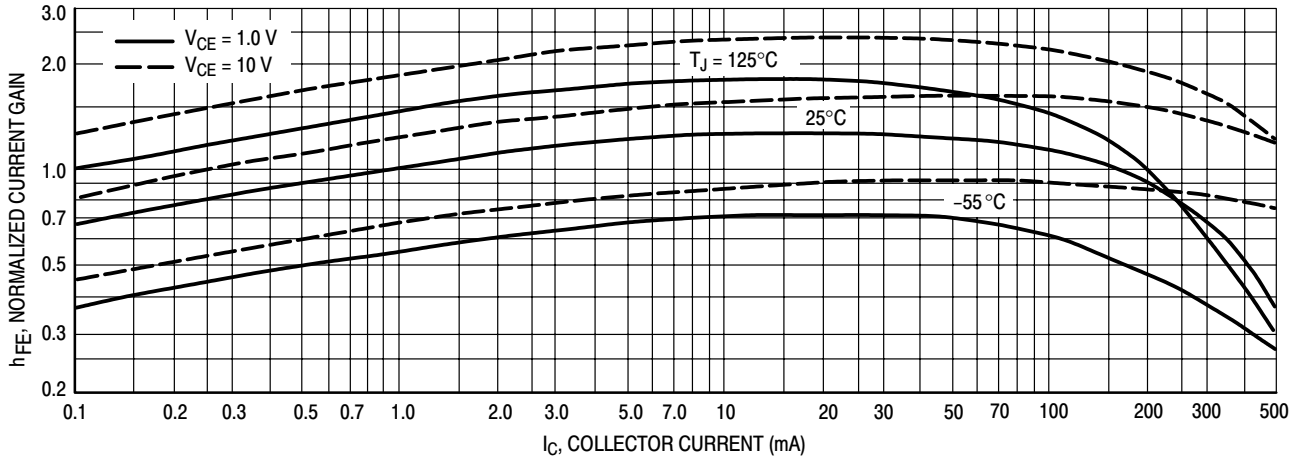


Figure 14. DC Current Gain

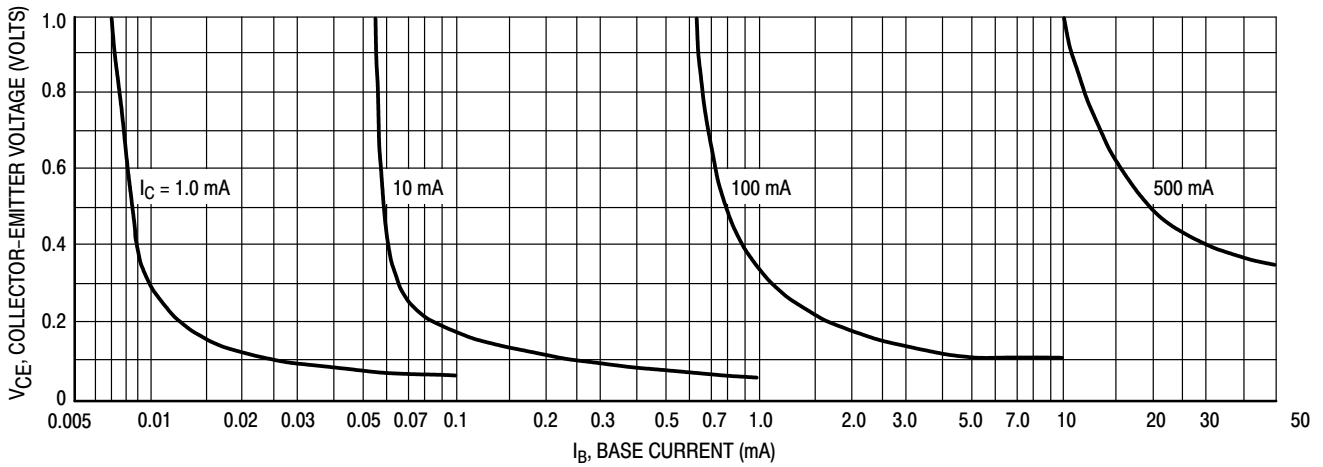


Figure 15. Collector Saturation Region

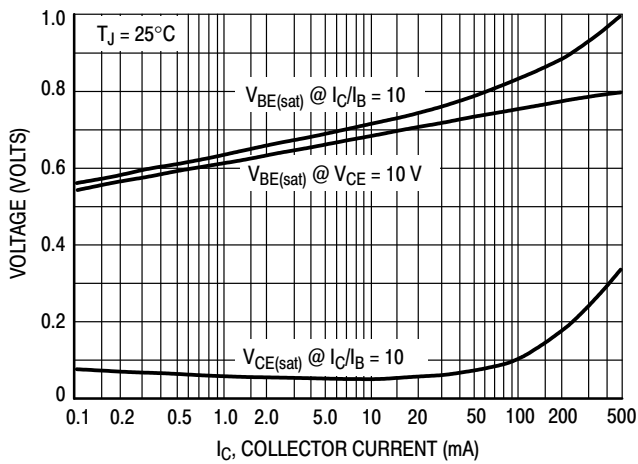


Figure 16. "On" Voltages

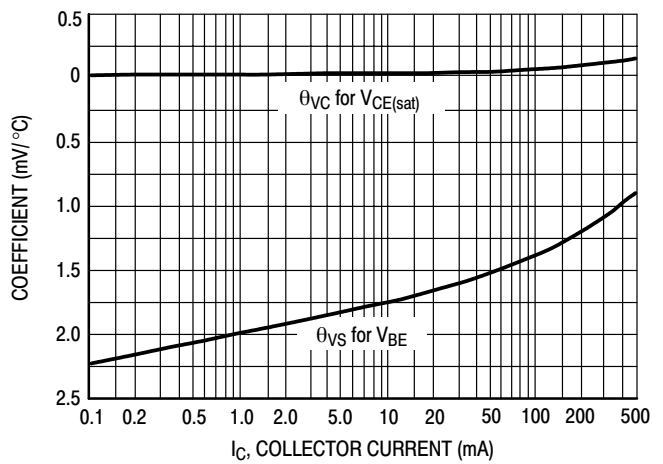
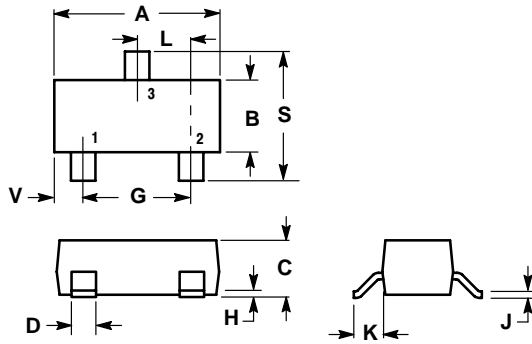


Figure 17. Temperature Coefficients

# MMBT4403LT1

## PACKAGE DIMENSIONS

CASE 318-08  
SOT-23 (TO-236)  
ISSUE AH



NOTES:

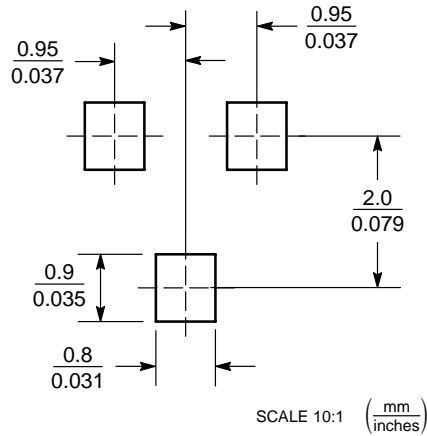
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 6:

- PIN 1. BASE
- EMITTER
- COLLECTOR

### SOLDERING FOOTPRINT\*



### SOT-23

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MMBT4403LT1

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